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Beam induced desorption Dr. Oleg B. Malyshev,

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Outline

- Photon simulated desorption
- Electron simulated desorption and BIEM
- Ion simulated desorption and ion induced pressure instability
- NEG coated vacuum chamber
- Cryogenic vacuum chamber: recycling and cracking



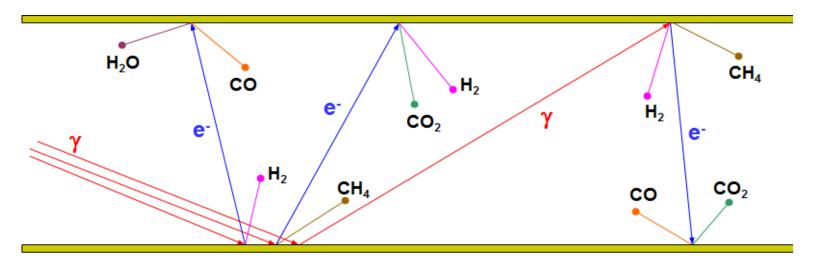
Photon stimulated desorption (PSD)



PSD

Photon stimulated desorption (PSD) is one of the most important sources of gas *in the presence of SR*.

- PSD can be considered as a two-step process:
- •first, photons with energy >10 eV cause the photoelectron emission,
- •then the photoelectron stimulate gas desorption.



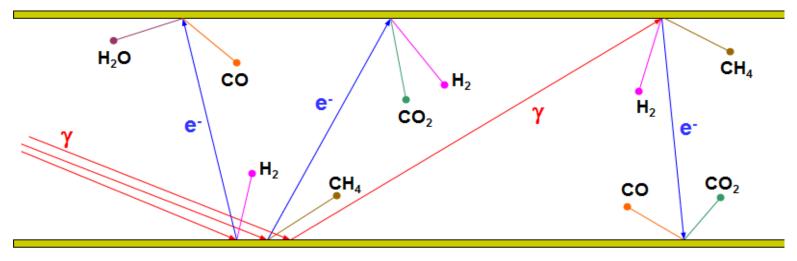
Gas molecules may desorb from a surface when and where *photoelectrons* leave and arrive at a surface



PSD yields

PSD yields are defined as a number of gas molecules desorbed from the surface per incident photon, η_{γ} [molecules/photon]:

$$\eta_{\gamma} \left[\frac{molecules}{photon} \right] = \frac{Q \left[Pa \cdot m^3 / s \right]}{k_B T \left[K \right] \Gamma \left[photon / s \right]},$$





What PSD depend on?

Similarly to thermal desorption, PSD depends on:

- Choice of material
- Cleaning procedure
- History of material
- Bakeout and vacuum firing
- Pumping time

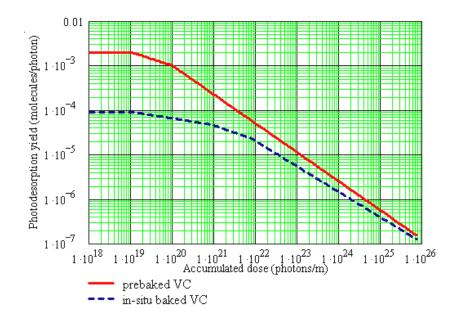
Additionally it depends on

- Energy of photons
- Photon flux
- Integral photon dose
- Temperature



PSD as a function of dose

Photodesorption yields, η (molecules/photon), as a function of accumulated photon dose, D, for different materials measured up to certain doses, these results are extrapolated for use in the design of new machines



Photodesorption yield as function of accumulated photon dose can be described as:

$$\eta = \eta_0 \left(\frac{D_0}{D}\right)^{\alpha}, \quad 0.65 < \alpha < 1$$

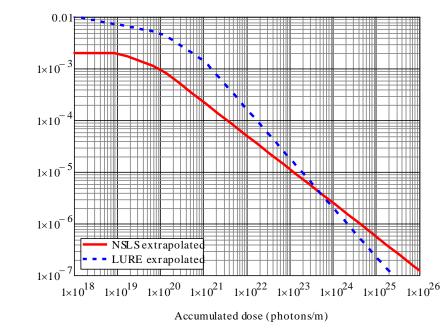
PSD yield for CO for prebaked and *in-situ* baked stainless steel vacuum chambers. Yields for doses higher then 10²³ photons/m (1 to 10 Amp·hrs for diamond) are extrapolations.



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PSD as a function of dose

Example of PSD yields for CO for unbaked and baked vacuum chambers as a function of accumulated photon dose D, based on results of experiments at NSLS [J. Vac. Sci. Technol. A 8, 2856 (1990)] and LURE [J. Vac. Sci. Technol. A 17 635 (1999)].



Photodesorption yield as function of accumulated photon dose can be described as:

$$\eta = \eta_0 \left(\frac{D_0}{D}\right)^{\alpha},$$

$$\alpha = 0.65 \text{ for } \varepsilon_c = 500 \text{ eV at NSLS}$$

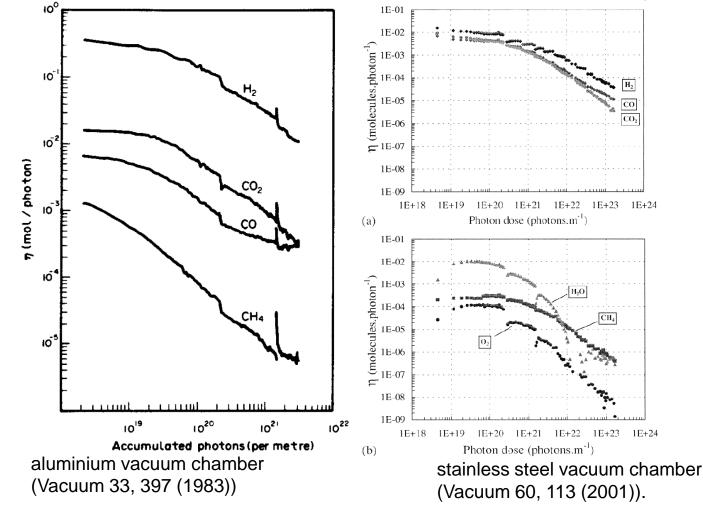
$$\alpha = 1 \text{ for } \varepsilon_c = 3.35 \text{ keV at LURE}$$

Yields for doses higher then 10^{23} photons/m (1 to 10 Amp·hrs for diamond) are extrapolations.



PSD as a function of dose

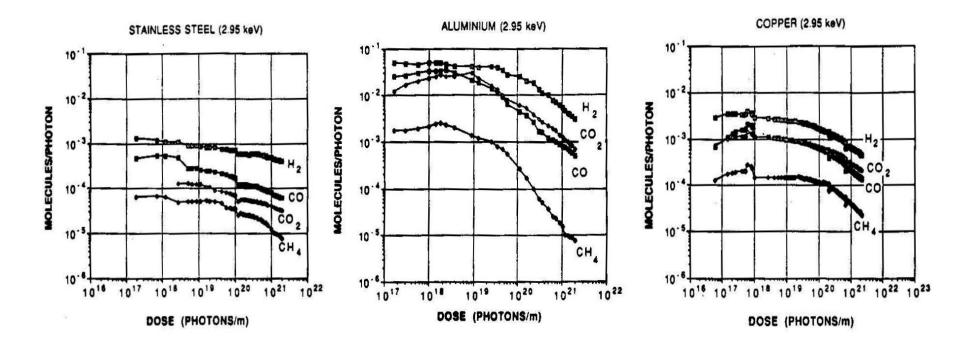
The PSD yield η for various gas species as a function of the accumulated photon dose at ε_c = 3.75 keV at DCI



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PSD yields from different materials as a function of photon dose

Photodesorption yields, η(molecules/photon), as a function of accumulated photon dose for different materials for Vacuum chamber (A. Mathewson, AIP Conf. Proc. 236 (1), 313 (1991))

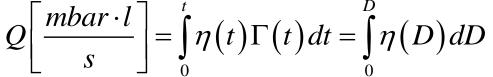




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Amount of desorbed gas as a function of photon dose

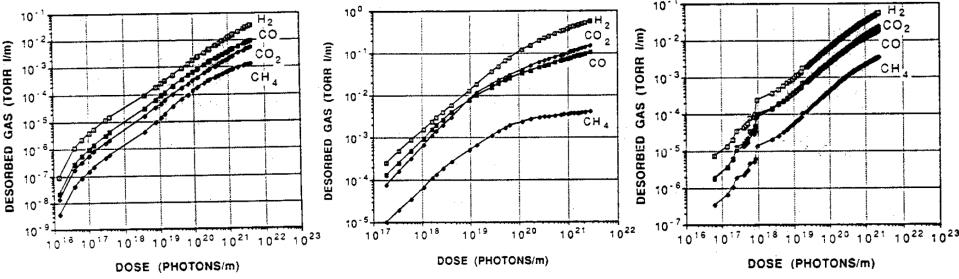
The same data can be analysed differently, amount of desorbed gas : $\begin{bmatrix} mbar \cdot l \end{bmatrix} \stackrel{t}{\leftarrow} (n) = \begin{pmatrix} D \\ \bullet \end{pmatrix}$



Stainless steel







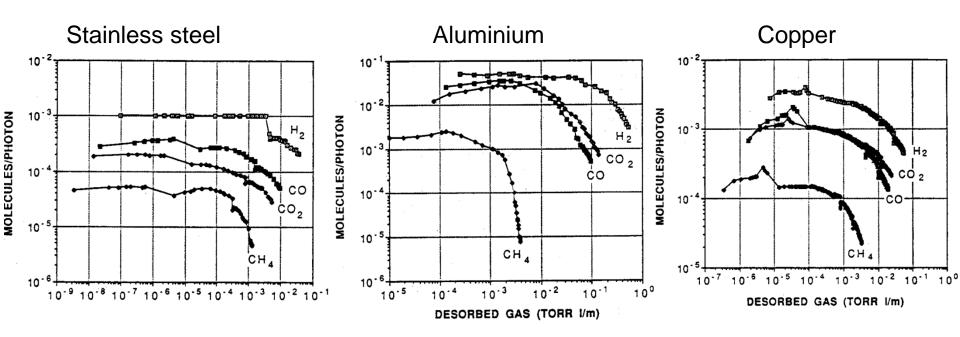
This information is important when the sorption pumps are used such as NEG cartridges or cryosorbers

O.B. Malyshev



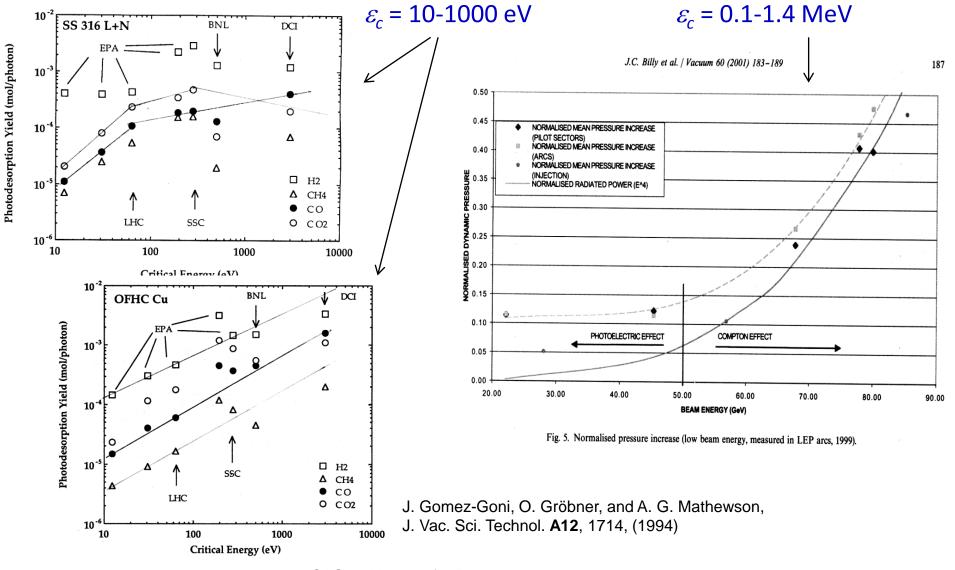
PSD as a function of amount of desorbed gas

The same data platted differently:



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AS PSD as a function of critical energy of SR

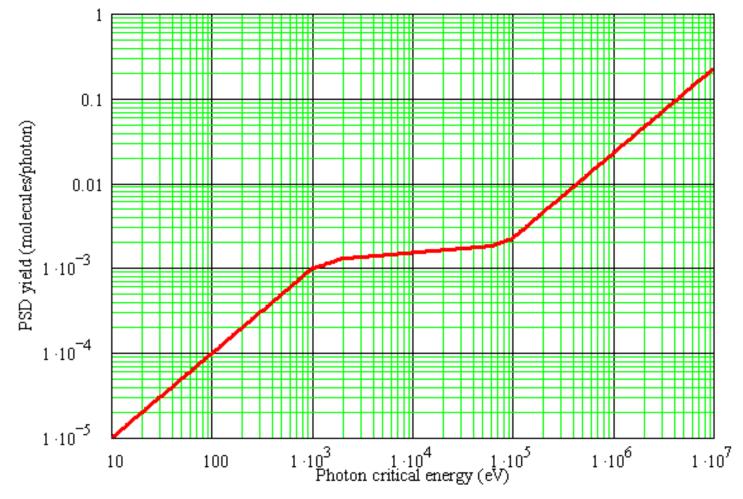


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AS PSD as a function of critical energy of SR



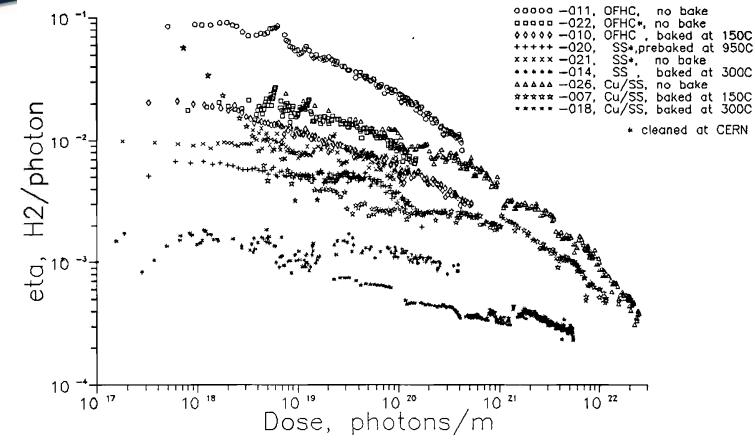
J. Vac. Sci. Technol. A 25(2007): 791-801



PSD: effect of bakeout

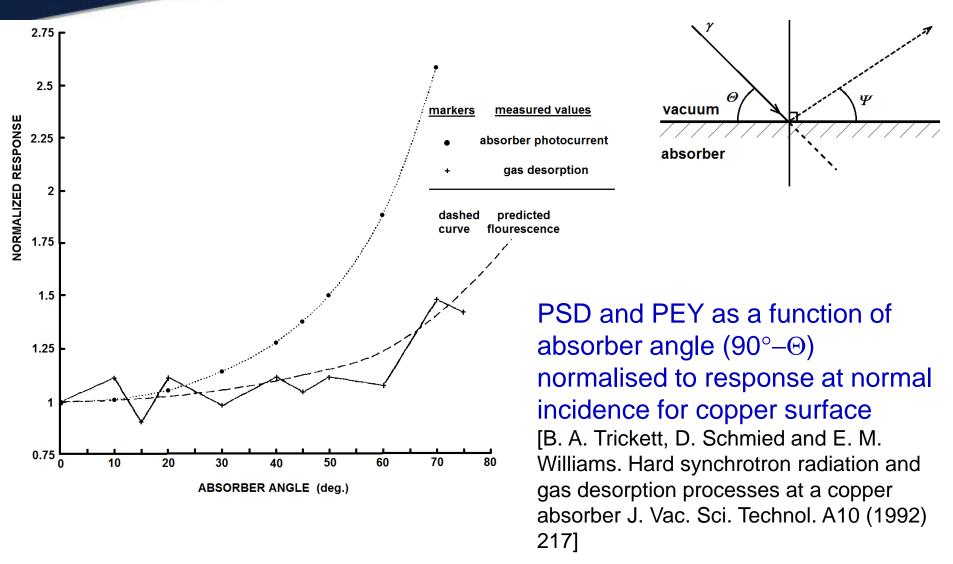
Bakeout	Impact	Comment
In-situ at 150 °C	reduction of $\eta_{\rm H2O}$ by 5-10 times;	Reducing bakeout temperature
for 24 hrs	reduction of initial PSD yields for	to 120 °C requires increasing of
	other species by 2-4 times	bakeout duration to a few days.
In-situ at 300-350 °C	reduction of initial $\eta_{\rm H2}$ by 10-20 times,	-
for 24 hrs:	for other species by 7-15 times	
Ex-situ at 250-300 °C	reduction of initial $\eta_{\rm H2}$ by 5-10 times,	keep in vacuum; minimise vent
for 24 hrs	for other species by 4-8 times	to air during installation; purge
		with dry air, N ₂ or noble gases
Vacuum firing at 950 °C	hydrogen depletion in the bulk of	Keep in vacuum or fill with N_2 or
for 1-2 hrs at P < 10 ⁻⁵	vacuum chamber material	noble gas.
mbar		
No in-situ bakeout after	reduction of $\eta_{\rm H2}$ by ~1.5-2 times	
vacuum firing		
In-situ bakeout after	reduction of $\eta_{\rm H2}$ by ~20-50 times	
vacuum firing		





The comparison of η_{H2} from OFHC, stainless steel (SS) and copper coated stainless steel samples with and without bakeout [O.B. Malyshev, PhD Thesis, Budker Institute of Nuclear Physics, Novosibirsk, 1995]

Effect of incident angle on PSD



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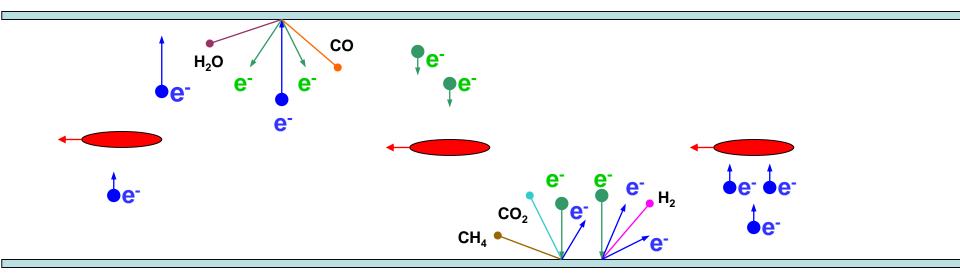


Electron stimulated desorption (ESD)





Electron stimulated desorption (ESD) could be an important sources of gas in case of electron beam bombardment, beam induced electron multipacting, or as a part of the PSD process *in the presence of SR*.



Gas molecules may desorb from a surface when and where *electrons* leave (with low energy) and arrive at a surface (with higher energy)

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ESD yields

ESD yields are defined as a number of gas molecules desorbed from the surface per incident electron, η_e [molecules/e⁻]:

$$\eta_{e}\left[\frac{molecules}{e^{-}}\right] = \frac{N_{molecules}}{N_{electrons}} = \frac{Q\left[Pa \cdot m^{3}/s\right]q_{e}\left[C\right]}{k_{B}T\left[K\right]I\left[A\right]},$$

where

- Q is a flux of molecules desorbed due to ion bombardment,
- *I* is the ion current,
- q_e is the elementary charge



What ESD depend on?

Similarly to PSD and thermal desorption, ESD depends on:

- Choice of material
- Cleaning procedure
- History of material
- Bakeout and vacuum firing
- Pumping time

Additionally it depends on

• Energy of electrons

impinging the surface

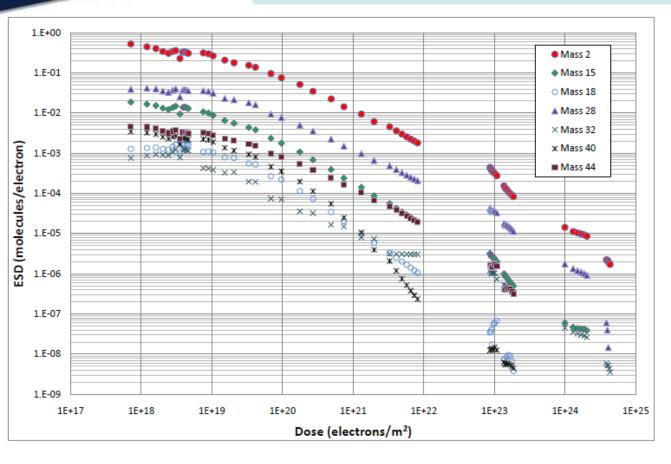
- Electron flux to the surface
- Integral electron dose
- Temperature

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ESD as a function of dose



ESD yield as function of accumulated photon dose can be described as:

$$\eta = \eta_0 \left(\frac{D_0}{D}\right)^{\alpha}$$

the exponent α lies between $0.5 \le a \le 1$

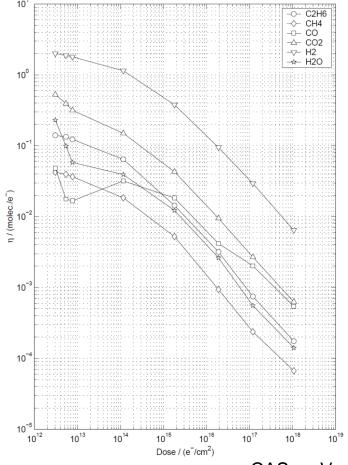
ESD yields of 316 LN stainless steel baked to 250 °C for 24 hours as a function of electron dose at electron energy Ee = 500 eV.

O.B. Malyshev and C. Naran. Vacuum 86 (2012), 1363-1366.

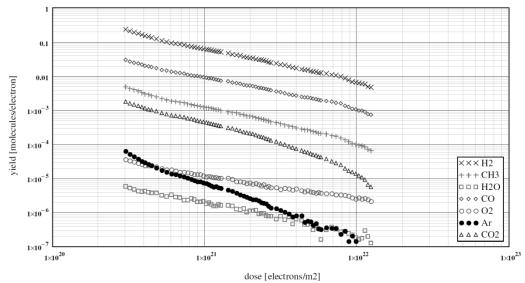


ESD from different materials

ESD yields of unbaked OFHC copper after 24-hour pumping as a function of electron dose at $E_e = 300 \text{ eV}$



ESD yields of aluminium alloy baked to 220 °C for 24 hours as a function of electron dose at electron energy $E_e = 500 \text{ eV}$

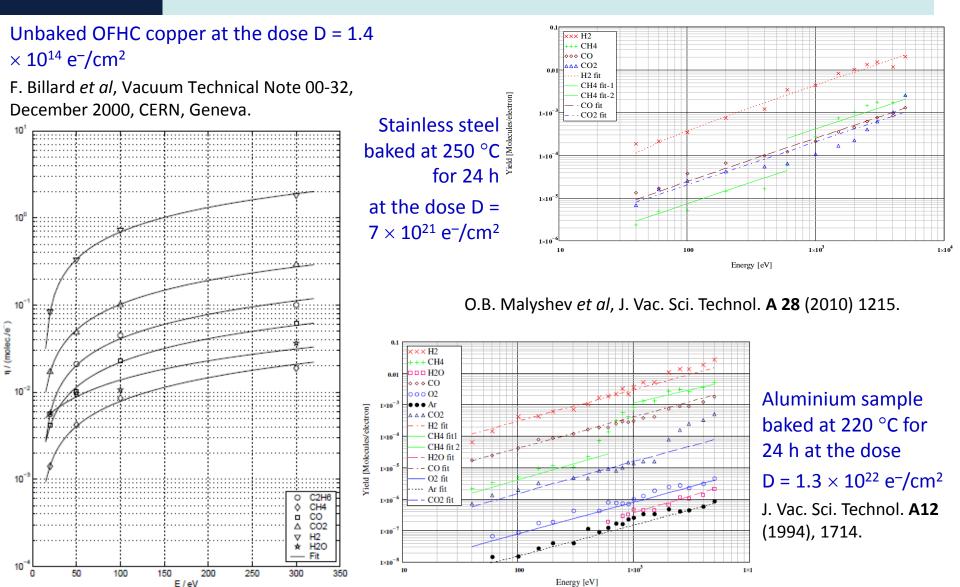


F. Billard *et al*, Some Results on the Electron Induced Desorption Yield of OFHC Copper. Vacuum Technical Note 00-32, December 2000, CERN, Geneva.

O.B. Malyshev et al, Vacuum 85 (2011) 1063-1066.

O.B. Malyshev

ASTe ESD as a function of electron energy

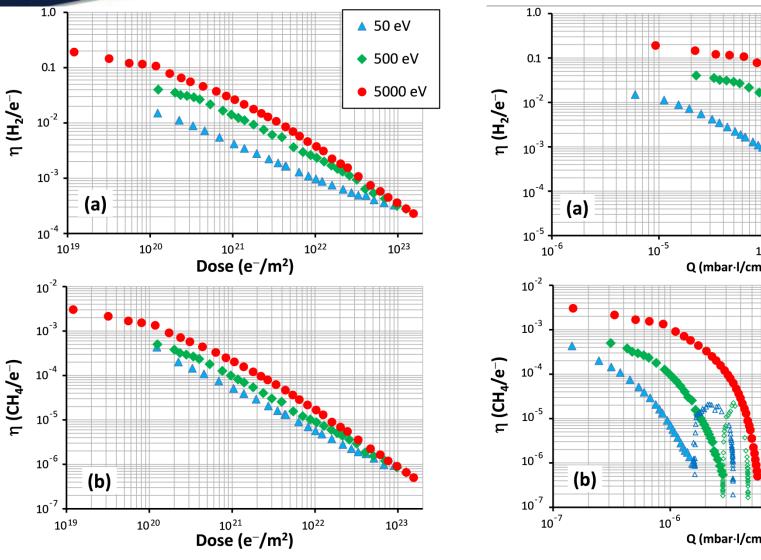


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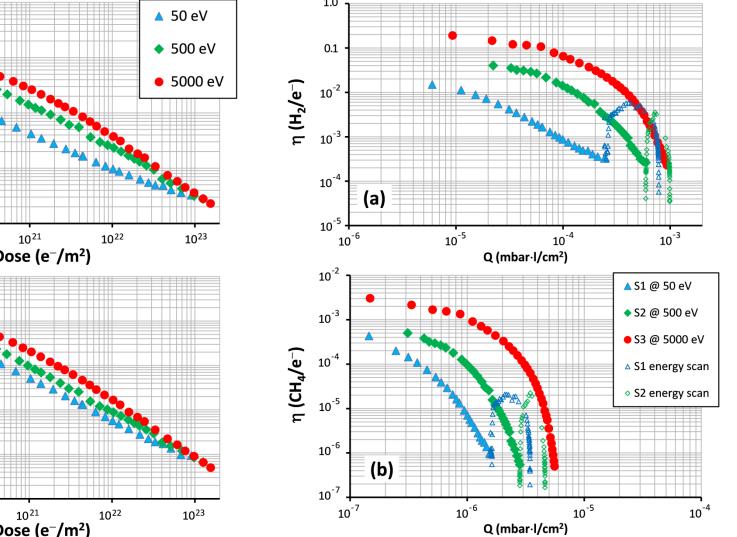
O.B. Malyshev

ESD as a function of electron energy Science & Technology Fa

316LN stainless steel baked at 250 °C for 24 h



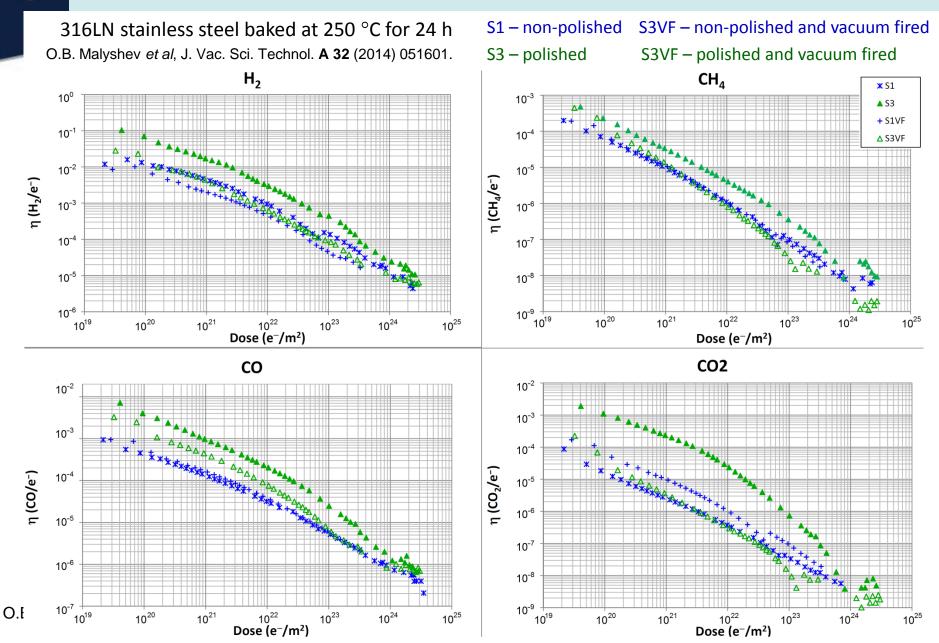
O.B. Malyshev et al, J. Vac. Sci. Technol. A 31 (2013) 031601.



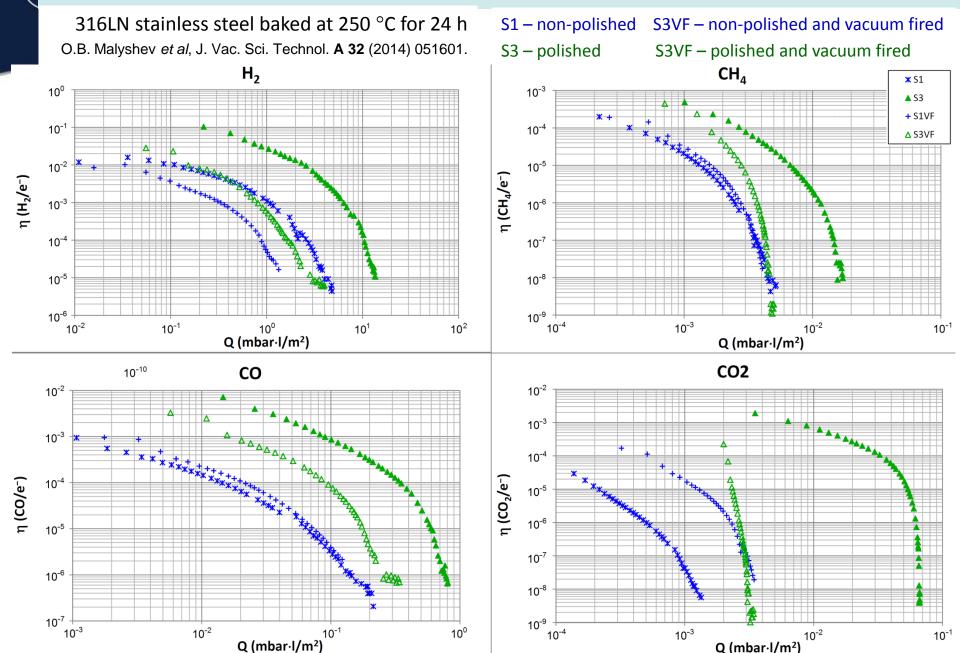
O.B. Malyshev

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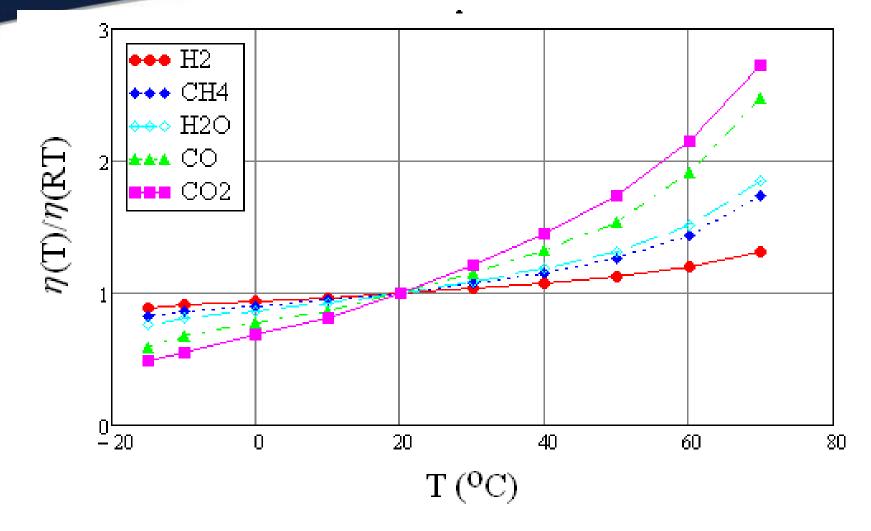
ESD from polished and vacuum fired tubes



ESD as a function of amount of desorbed gas



ASTe **ESD** as a function of wall temperature



O.B. Malyshev, C Naran. Vacuum 86 (2012) 1363.



Ion stimulated desorption (ISD)

ASTeC Ion Induced Pressure Instability

When the *positive charged beam particles* colliding with residual gas molecules ionise them, these ions are accelerated towards the vacuum chamber wall. This causes ion induced gas desorption, the pressure rises and more molecules will be ionised, accelerated and bombard the wall...

$$n = \frac{Q}{S_{eff} - \chi \frac{\sigma I}{e}} = \frac{Q}{\chi \frac{\sigma}{e} (I_c - I)} \qquad I_c = \frac{S_{eff} e}{\chi \sigma}$$

where Q = gas desorption, $S_{eff} = \text{effective pumping speed},$ $\chi = \text{ion induced desorption yield}$ $\sigma = \text{ionisation cross section},$

l = beam current.

$$\begin{array}{c} + & H_2^+ & H_2 \\ \hline & & CO_2 \\ \hline & & CO_2 \end{array}$$

When
$$I \to I_c$$
 (or $S_{eff} \le \chi \frac{\sigma I}{e}$)

then gas density (pressure) increases dramatically!



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ISD

Ion stimulated desorption (ISD) can be a significant gas source in a vacuum system where the ion beam bombards the surface. There is very little data, most work has been done at CERN.

Similarly to thermal desorption, PSD and ESD, the ISD depends on: choice of material, cleaning procedure, history of material and pumping time.

It is also depends on:

- Mass, charge and energy of ions impacting the surface
- Ion flux to the surface
- Integral ion dose
- Temperature



ISD yields

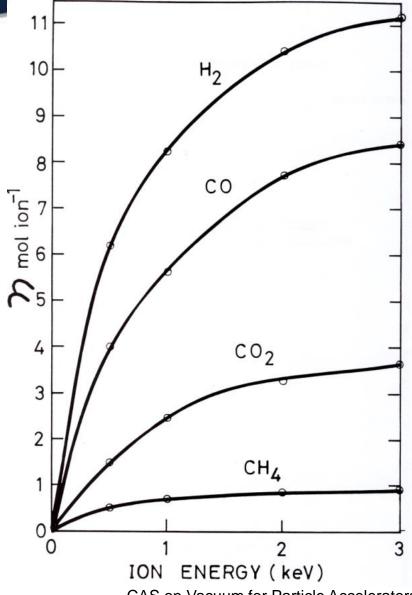
ISD yields, defined as a number of gas molecules desorbed from the surface per incident ion, χ (molecules/ion), :

$$\chi \left[\frac{molecules}{ion} \right] = \frac{N_{molecules}}{N_{ions}} = \frac{Q \left[Pa \cdot m^3 / s \right] q_e \left[C \right] n_q}{k_B T \left[K \right] I \left[A \right]},$$

where

- Q is a flux of molecules desorbed due to ion bombardment,
- *I* is the ion current,
- q_e is the elementary charge and
- n_q is the ion charge number

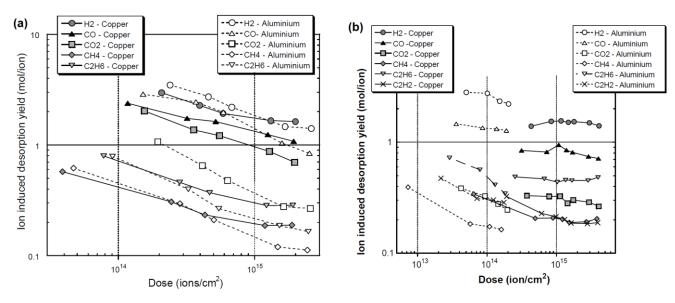
ISD yields as a function of ion energy



A.G. Mathewson. Ion induced desorption coefficients for titanium alloy, pure aluminum and stainless steel. CERN-ISR-VA/76-5 (1976).

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ISD as a function of dose



ISD yield as function of accumulated ion dose can be described as:

$$\chi_i(D) = \chi_i(D^*) \left(rac{D^*}{D}
ight)^{\!\!lpha};$$

The ISD yields as a function of accumulated ion dose from (a) as-received and (b) baked aluminium and copper samples bombarded with argon ions at 5 keV.

M.P. Lozano. Ion-induced desorption yield measurements from copper and aluminium. Vacuum **67** (2002) 339.

the exponent α lies

between $0.3 \le \alpha \le 0.5$ for as-received samples and

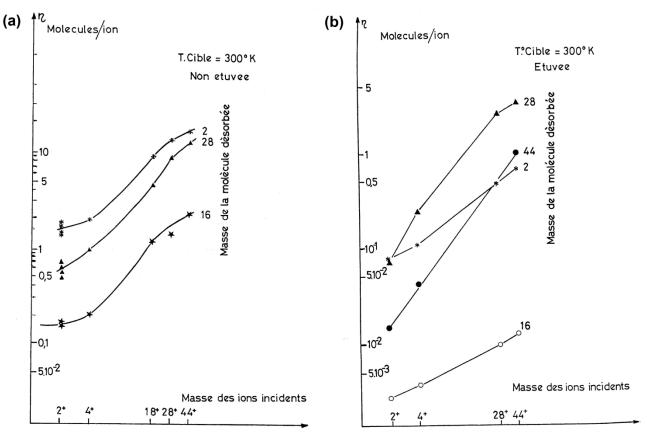
between $0 \le \alpha \le 1/3$ for baked samples

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ISD as a function of ion mass

ISD yield from (a) unbaked and (b) baked stainless steel sample as a function of incident ion mass



N. Hilleret. Influence de la nature des ions incidents sur les taux de desorption par bombardement ionique de molécules adsorbées sur une surface d'acier inoxydable. CERN-ISR-VA/78-10 (1978).

O.B. Malyshev



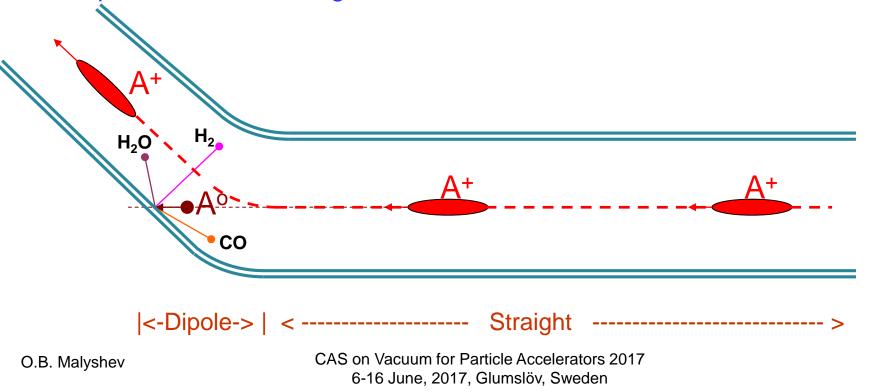
Heavy ion stimulated desorption (HISD)



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Heavy Ion Induced Pressure Instability

The *heavy ion beam particles* colliding with residual gas molecules may lose or trap an electron and be *lost* in the bending magnet. These very high energy ions or neutrals bombard the vacuum chamber wall which results in a very high desorption yield (*up to a few thousands molecules per ion*). This causes further gas desorption, resulting in a pressure rise and more lost beam particles bombarding the wall...





HISD

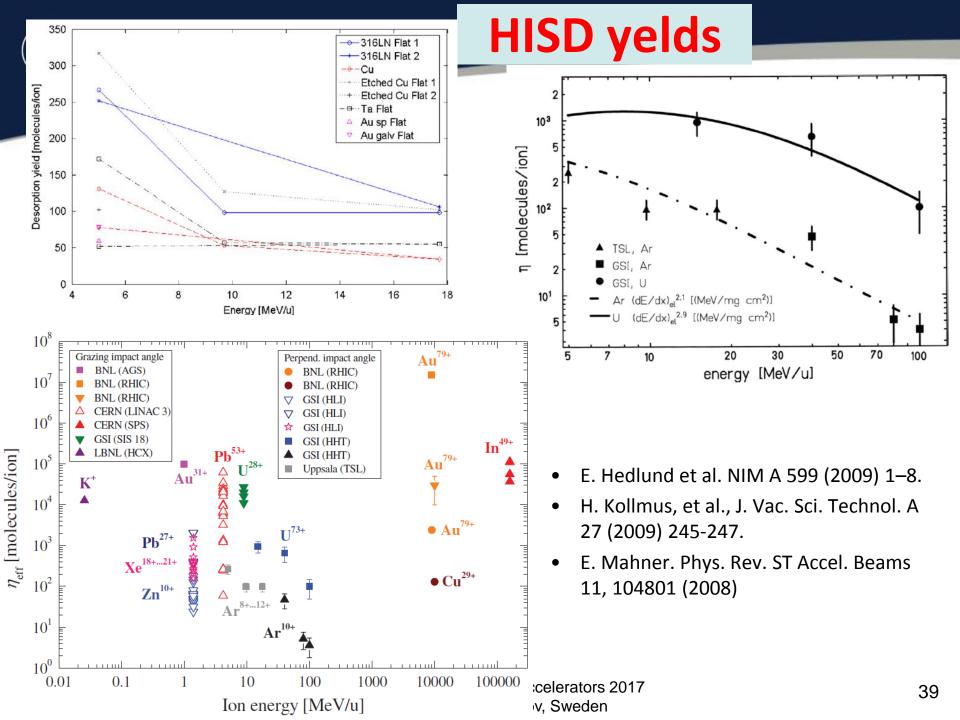
Heavy ion stimulated desorption (ISD) is a key parameter to model pressure instability in high intensity ion machines like FAIR at GSI, LURE at CERN, RHIC at BNL. It can be a significant source of gas in a vacuum system where the ion beam bombards the surface.

There is very little data, most work has been done at GSI and CERN.

Similarly to thermal desorption, PSD and ESD and ISD, the HISD depends on: choice of material, cleaning procedure, history of material and pumping time.

It is also depends on:

- Mass, charge and energy of heavy ions impacting the surface
- Ion flux to the surface





NEG coated vacuum chamber

Two concepts of the ideal vacuum chamber

Traditional:

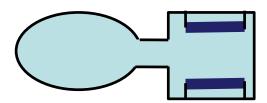
- <u>surface which outgasses as little as</u> <u>possible ('nil' ideally)</u>
- surface which *does not pump* otherwise that surface is contaminated over time
- Results in
- Surface cleaning, conditioning, coatings
- Vacuum firing, *ex-situ* baling
- Baking *in-situ* to up to **300°C**
- Separate pumps

'New' (C. Benvenuti, CERN, ~1998):

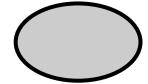
- <u>surface which outgasses as little as</u> possible ('nil' ideally)
- a surface which *does pump*, however, will not be contaminated due to a very low outgassing rate

Results in

- NEG coated surface
- There should be no un-coated parts
- Activating (baking) *in-situ* at **150-180°C**
- Small pumps for C_xH_y and noble gases





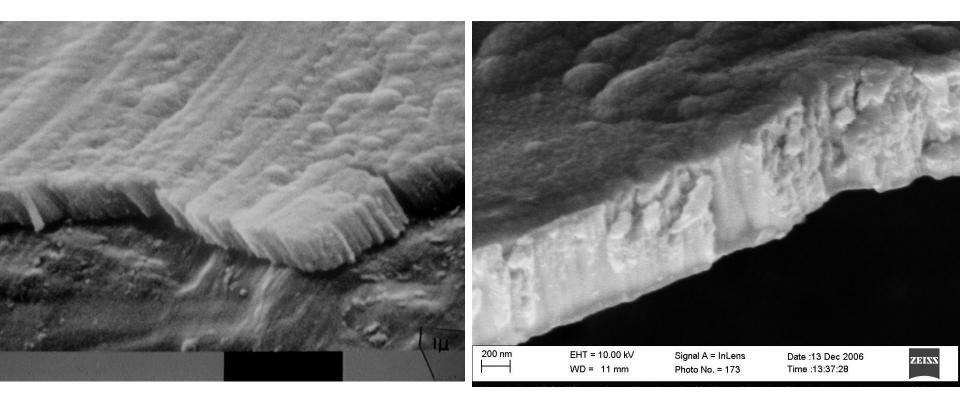




SEM images of films (film morphology)

columnar

dense



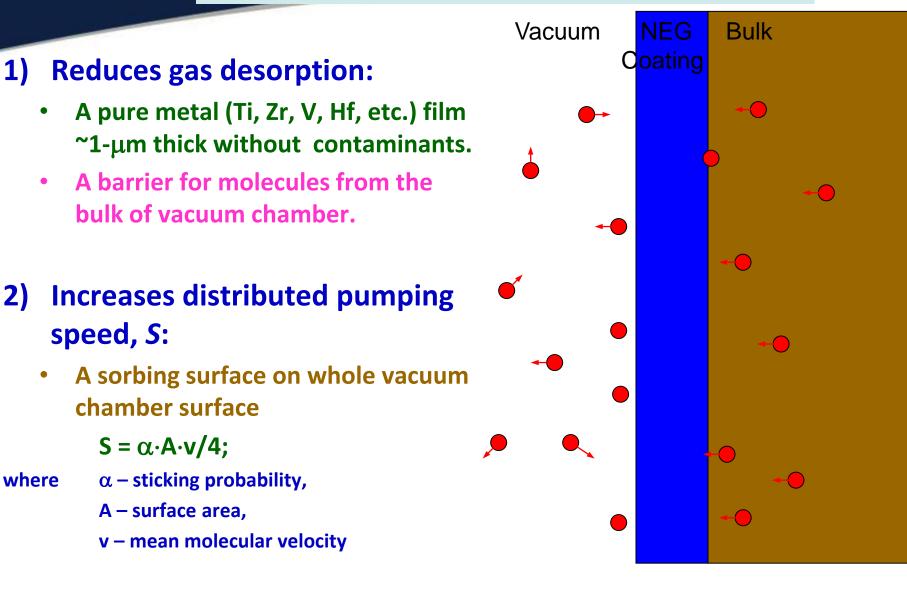
O.B. Malyshev, R. Valizadeh, J.S. Colligon et al. J. Vac. Sci. Technol. A 27 (2009), p. 521.

O.B. Malyshev



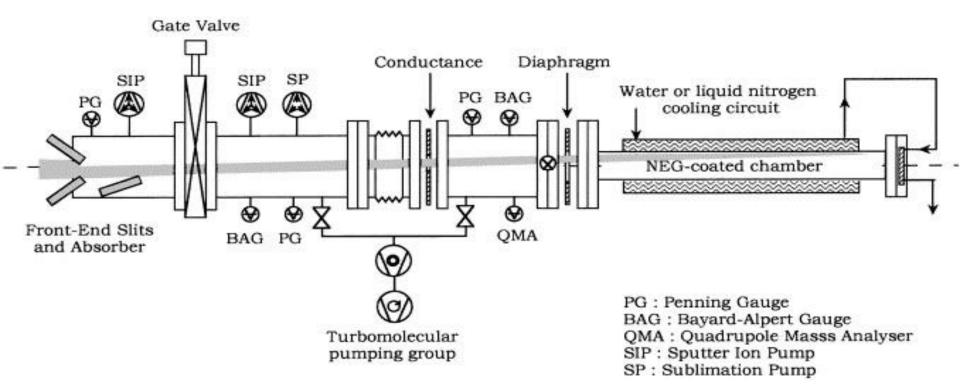
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What NEG coating does?



First experiments with NEG coating: Conductance method

- Samples coated with Ti-Zr-V at CERN (Switzerland)
- Experiments on a SR beamline at ESRF (France)

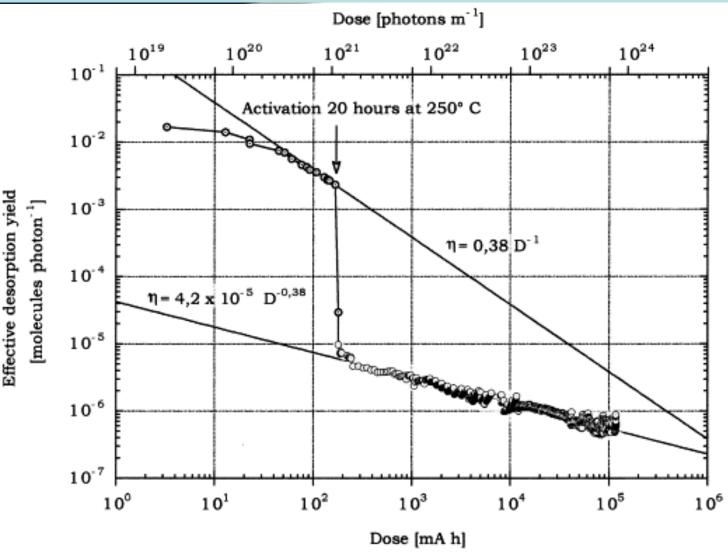


Dynamic pressure rise for the Stainless Steel (baked at 300°C for 24 hrs) and TiZrV coated vacuum chambers (activated at 190°C for 24 hrs)

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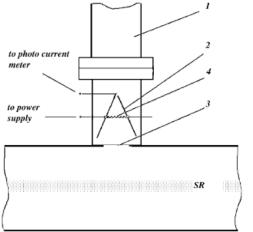


First experiments with NEG coating

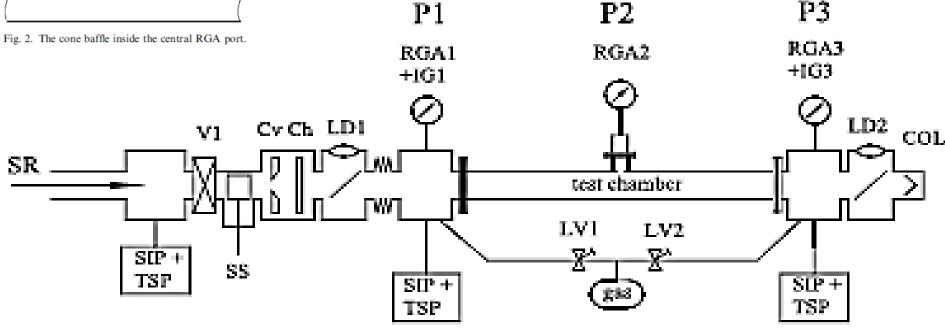


P. Chiggiato, R. Kersevan, Vacuum 60 (2001) 67.

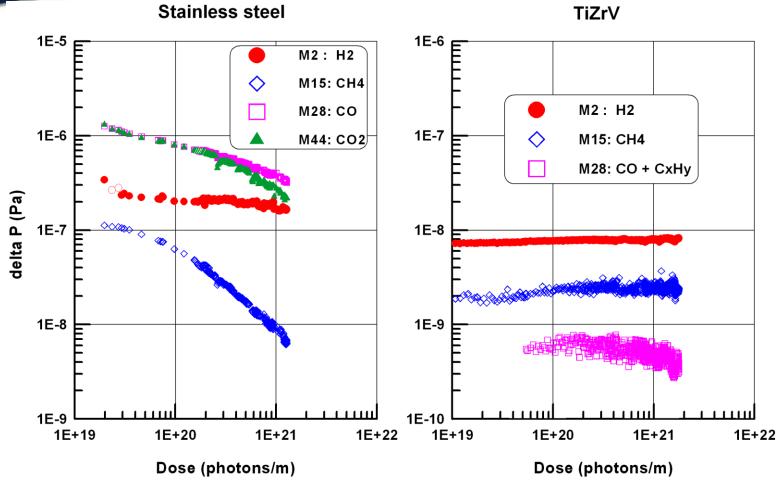
First experiments with NEG coating: Three-gauge method



- Samples coated with Ti-Zr-V at CERN (Switzerland)
- Experiments on a SR beamline at BINP (Russia)



Comparison of PSD from 316LN and NEG coated vacuum chamber under SR



Dynamic pressure rise for the Stainless Steel (baked at 300°C for 24 hrs) and TiZrV coated vacuum chambers (activated at 190°C for 24 hrs)

Comparison of PSD from 316LN and NEG coated vacuum chamber under SR

	α	ΔΡ,	η,	α	ΔΡ,	η,
Gas		[Torr]	[molecules/		[Torr]	[molecules/
			photon]			photon]
	NEG TiZrV coated vacuum chamber					
	Before activation			After activation at 190°C for 24 hrs		
H ₂	0	$4 \cdot 10^{-8}$	$1 \cdot 10^{-3}$	0.007	$5 \cdot 10^{-11}$	$1.5 \cdot 10^{-5}$
CH ₄	0	$2.5 \cdot 10^{-8}$	$2.5 \cdot 10^{-4}$	0	$1.5 \cdot 10^{-11}$	$2 \cdot 10^{-7}$
$C_x H_y(28)$	—	—	_	0	$<4 \cdot 10^{-12}$	<3.10-8
CO (28)	0	$6 \cdot 10^{-8}$	$5 \cdot 10^{-4}$	0.5	$< 2 \cdot 10^{-12}$	$<1.10^{-5}$
CO ₂	0	$5 \cdot 10^{-8}$	3.10-4	0.5	$<5 \cdot 10^{-13}$	$< 2 \cdot 10^{-6}$
	Stainless steel vacuum chamber baked at 300°C for 24 hrs					
	Initially			After $1 \cdot 10^{21}$ photons/m		
H ₂	—	$3 \cdot 10^{-9}$	$8 \cdot 10^{-5}$	—	$1.5 \cdot 10^{-9}$	$4 \cdot 10^{-5}$
CH ₄	—	$8 \cdot 10^{-10}$	$1 \cdot 10^{-5}$		$6.5 \cdot 10^{-11}$	8·10 ⁻⁷
СО	_	$1 \cdot 10^{-8}$	$8 \cdot 10^{-5}$		$3 \cdot 10^{-9}$	$2.5 \cdot 10^{-5}$
CO ₂	_	$1 \cdot 10^{-8}$	$7 \cdot 10^{-5}$	_	$2 \cdot 10^{-9}$	$1.5 \cdot 10^{-5}$

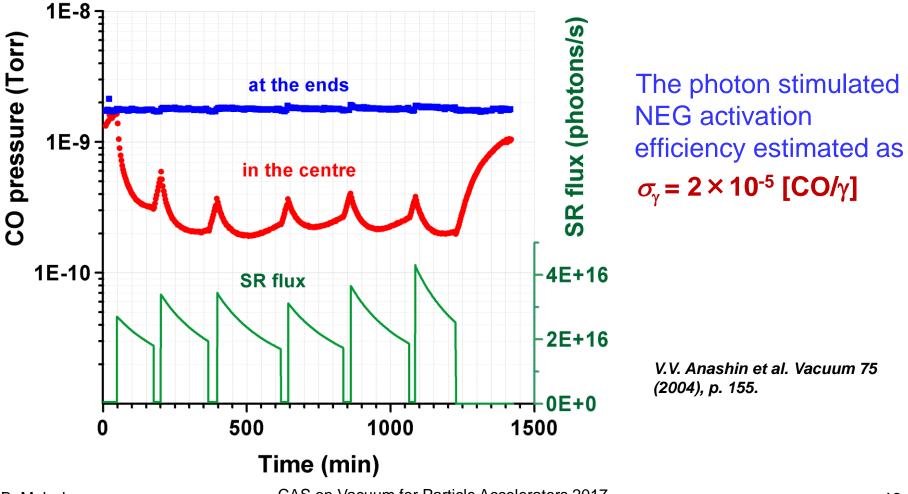
V.V. Anashin et al. Vacuum 75 (2004), p. 155.

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SR Induced Pumping

NEG TiZrV coated surface was saturated with CO (i.e. no pumping speed) then exposed to SR





ASTeC **NEG coating in accelerators**

- First used in the ESRF (France);
- ELETTRA (Italy);
- Diamond LS (UK);
- Soleil (France) first fully NEG coated;
- LHC (Switzerland) longest NEG coated vacuum chamber;
- SIS-18 (Germany); MAX-IV (Sweden)
- and many others.

Meanwhile:

- > NEG film capacity for CO and CO_2 is ~1 ML:
 - > If P = 10^{-9} mbar then 1 ML can be sorbed just in ~ 10^3 s;
 - Lab measurements of different NEG coatings often don't repeat CERN's data on sticking probability and capacity;

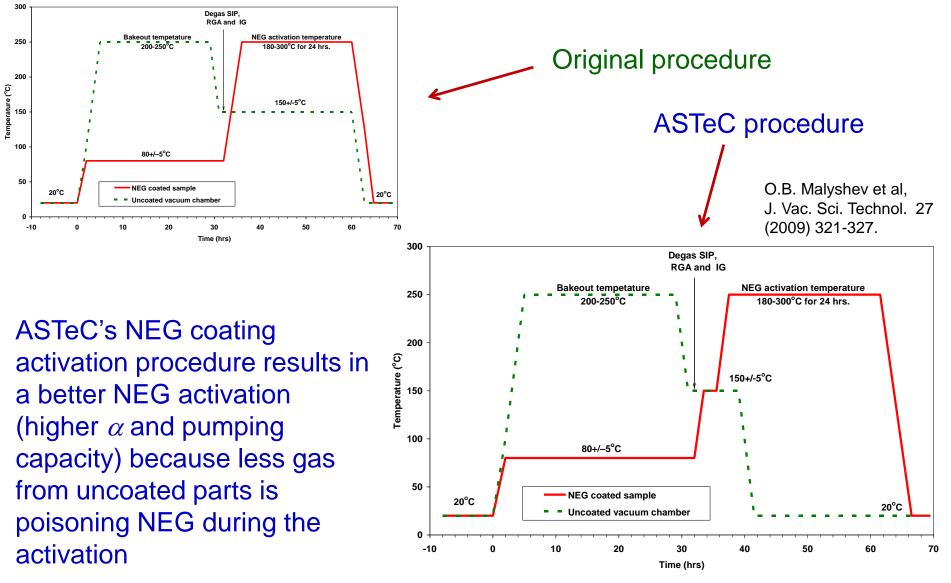
However, NEG coated parts of accelerators work well.



What is required:

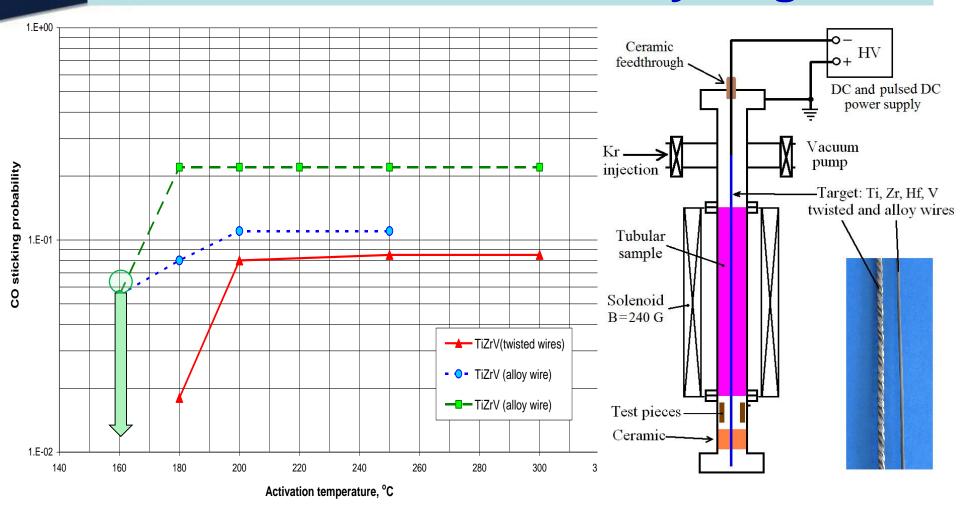
- Input data for accelerator design:
 - $\eta(D,E,T_a)$, $\alpha(M,T_a)$, pumping capacity;
- Better understanding:
 - what and why;
 - practical 'do's and 'don't's;
- Further development of this coating:
 - lower η, T_a, SEY;
 - higher α(M), pumping capacity;
 - optimising for an application.

NEG coating activation procedure



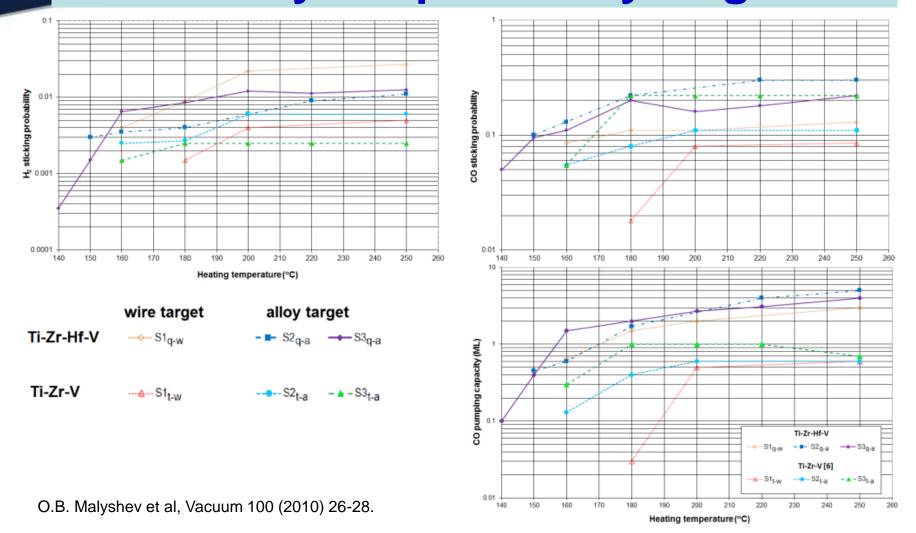
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Reducing activation temperature: Twisted wires vs. alloy target



R. Valizadeh et al, J. Vac. Sci. Technol. 28 (2010) 1404-1412.

Reducing activation temperature: ternary vs quaternary target





Pressure in the accelerator vacuum chamber

 Improving pumping properties is limited:

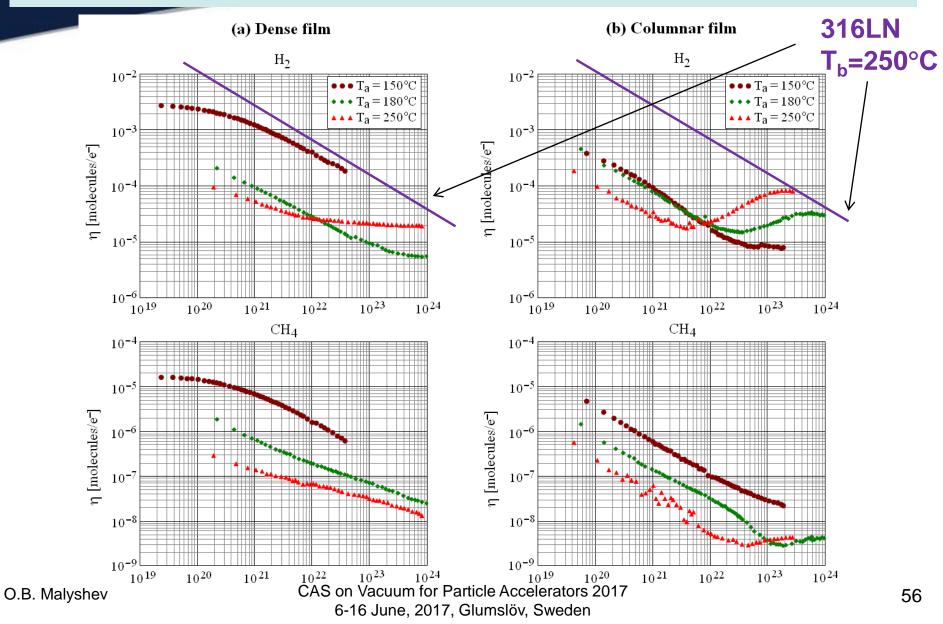
$$\label{eq:alpha} \begin{split} \alpha \leq \mathbf{1} \\ 0.005 < \alpha_{H2} < 0.01 \\ 0.1 < \alpha_{CO} < 0.5 \\ 0.4 < \alpha_{CO2} < 0.6 \end{split}$$

 Reducing the desorption yields η in orders of magnitude is a realistic task

 $P \propto \frac{\eta}{\alpha}$

where η - desorption yield α - sticking probability

ESD yield from NEG coated samples



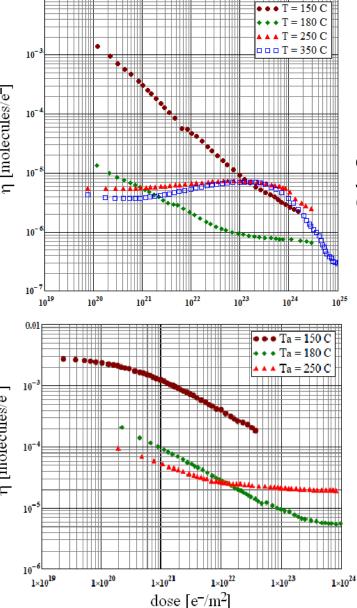
H2 ESD from NEG coated vacuum fired 316LN

(a) Columnar film 10 0.01 = 180 C T = 250 C 10 10 η [molecules/e⁻] 10 10-6

Vacuum fired η [molecules/e⁻]

No vacuum firing

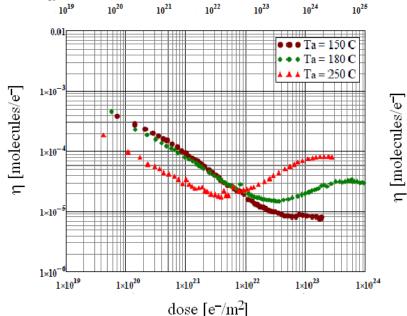
10

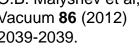


(b) Dense film

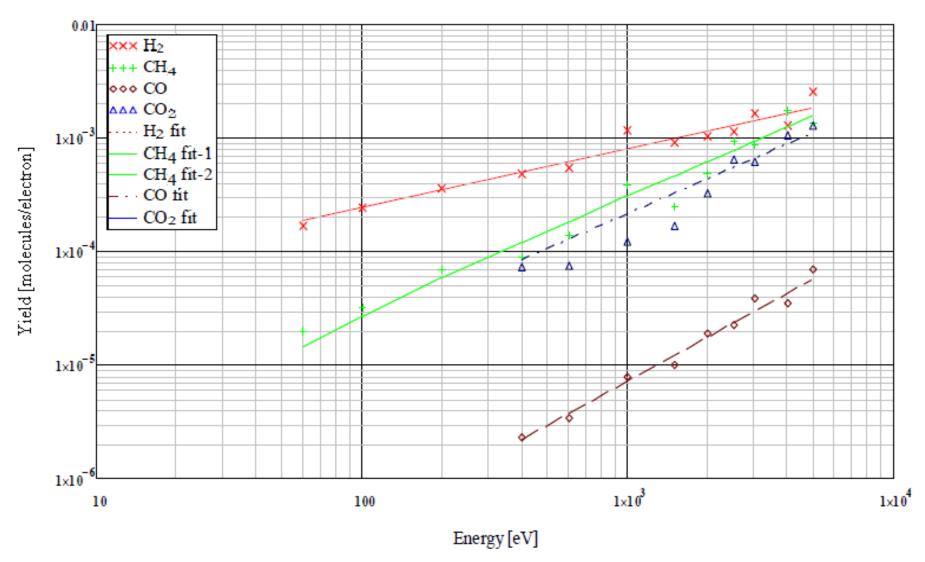
O.B. Malyshev et al, J. Vac. Sci. Technol. 32 (2014) 061601.







η(E_{e-}) for different gases for NEG coating

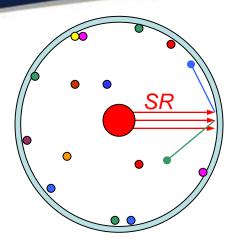


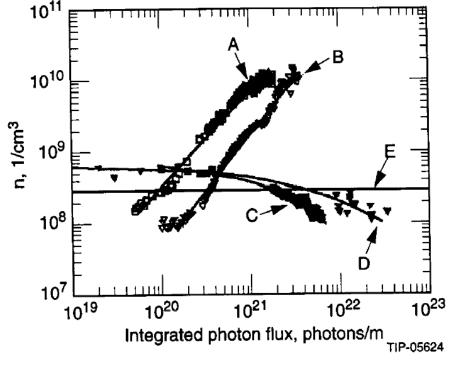


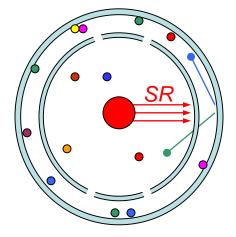
Cryogenic beam vacuum chamber

Vacuum Chamber at Low Temperature: PSD and Recycling

A and B are vacuum chamber without a liner







- C and D are experiments with a liner with pumping holes
- E is the beam lifetime limit

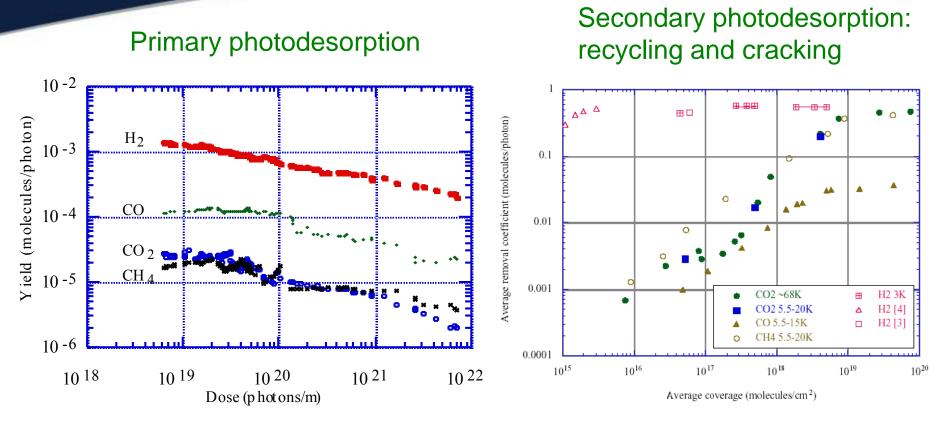
Figure 2. Dynamic H₂ density measured at the center of the beam tube with and without liner. The density is normalized to $1 \cdot 10^{16}$ photons/m/s.

V. Anashin et al. SSCL-Preprint-517 Rev.2, Apr 1994. V. Anashin et al. JVST A12 (1994), p. 2917.

Low temperature does not necessary provides good vacuum in a vacuum chamber!

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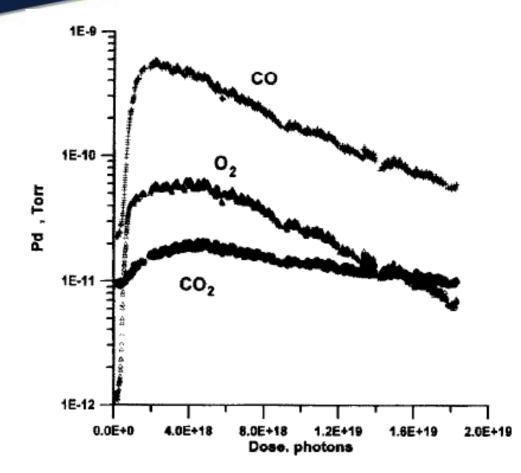
Vacuum Chamber at Low Temperature



Photodesorption yield at 77 K as a function of photon dose

Average removal coefficient as a function of surface coating

Cracking of cryosorbed CO₂ molecules by SR



- About 10³ monolayers of CO₂ were condensed
- CO is the main gas during SR
- O₂ is ~10 times lower
- CO₂ is ~30 times lower

$$2CO_2 + \tilde{\gamma} \rightarrow 2CO + O_2$$

V. Anashin et al, NIM A (1998), p. 258.

Fig. 3. The dynamic pressure dependance on the photon dose for CO, O_2 and CO₂ in the experiment with an average coverage of $8.2 \cdot 10^{17}$ molecules/cm².

Vacuum Chamber at Low Temperature: Molecular Cracking

There are four main photodesorbed gases in a cryogenic vacuum chamber: H_2 , CH_4 , CO and CO_2 , and two of them $(CH_4 \text{ and } CO_2)$ can be cracked by photons, $\tilde{\gamma}$:

$CH_4 + \widetilde{\gamma} \rightarrow C + 2H_2$ and $2CO_2 + \widetilde{\gamma} \rightarrow 2CO + O_2$

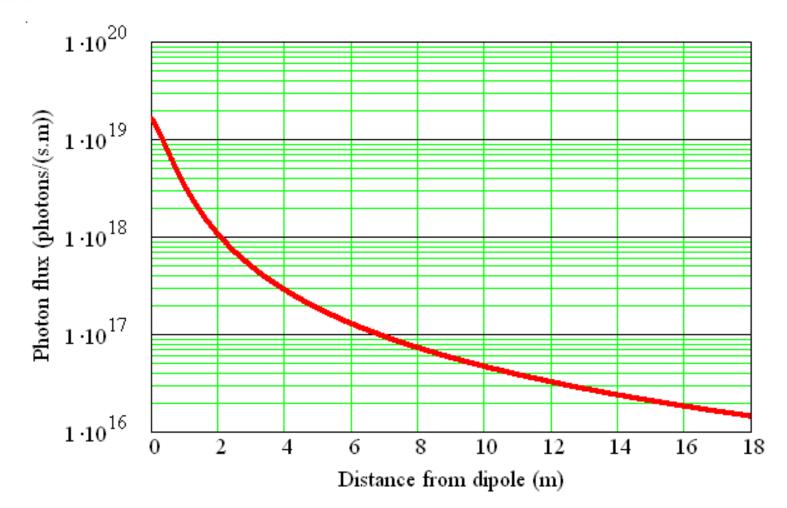
The additional amount of H_2 , CO and O_2 appears in a vacuum chamber due to photo-cracking of CH_4 and CO_2 . The efficiency of photo-cracking of CH_4 and CO_2 is about 10 times higher then CH_4 and CO_2 desorption from their cryosorbant!



How to use the experimental data in accelerator design

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=> This is for an ideal orbit and is very sensitive to the real beam position

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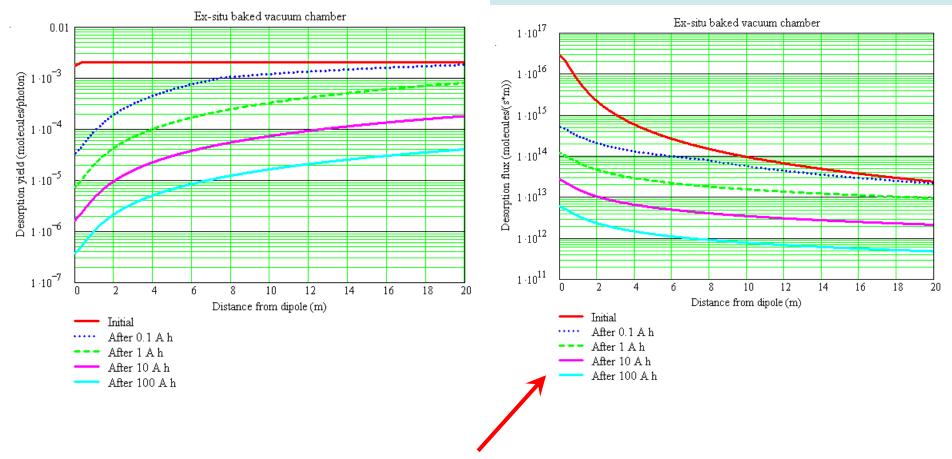


0.01 Photodesorption yield (molecules/photon) ·10⁻³ ---------------· ·10⁻⁴ ·10⁻⁵ ++++++ -----------√-10^{−6} ----- 1.10^{-7} prebaked VC in-situ baked VC $\eta = \eta_0 \left(\frac{D_0}{D}\right)^{\alpha}, \quad 0.65 < \alpha < 1$

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PSD yield and flux as a function of distance from a dipole magnet



=> These data for each gas can be used in the gas dynamics model.
 => Uncertainty in desorption flux is less than in photon flux and desorption yield

Final remarks: Vacuum is not an exact science

- There are a number of uncertainties in desorption yields:
- Desorption yields may differ (by factor 2 or even more) for vacuum components made of the same material after exactly the same cleaning procedure and treatments
- Results of Experiments:
 - 10-20% accuracy for all gauges at UHV
 - RGA calibration procedure can lead to an error: up to a factor 5 with a Faraday cap or a factor 10 with SEM
 - Modelling error (from 0.5% to a factor 2 or even more)
- Approximations: extending of experimental results on a few order of magnitude, it is just a reasonable guess!

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